



MICROELECTRONICS — SPACE PARK FOUNDRY

A leader in production, prototyping, research and development of microelectronics

Northrop Grumman's Microelectronics Center is comprised of two U.S.-based government-Trusted foundries and advanced packaging facilities. We design and deliver millions of critical microelectronics annually to support next-generation defense and commercial systems. From design to fabrication, our mission-tailored microelectronics solutions deliver unparalleled performance for any application.

DOMINATING THE ELECTROMAGNETIC SPECTRUM FROM RF TO THz WITH COMPOUND SEMICONDUCTORS

Space Park has a full suite of space qualified compound semiconductor technologies used in national asset space programs and commercial applications.

- Gallium Nitride (GaN) HEMT: High power and high survivability low noise applications through 100GHz
- Gallium Arsenide (GaAs) HEMT: Linear power and low noise applications through 100GHz
- Indium Phosphide (InP) HBT: High speed digital and mixed signals applications through 300 GHz
- Indium Phosphide (InP) HEMT: Low noise and high Frequency applications up to 1THz
- Wafer Level Packaging for chip scale hermetic packages and 3D Heterogeneous Integration (3DHI)
- Diverse Accessible Heterogenous Integration (DAHI)

THE GAN DIFFERENCE: POWER PERFORMANCE THROUGH MMW FOR DUAL USE APPLICATIONS

Space Park's qualified production GaN processes provides linear power through W-band. The technology is engineered to provide reliable performance with high gain and bandwidth for your most discriminating RF and mmW applications.

**NORTHROP
GRUMMAN**



**AWARDED COOLEST
THING MADE IN CA**
for THz chip



20,000 SQUARE FEET
of cleanroom manufacturing space



GUINNESS WORLD RECORD
for fastest microchip transistor



CONTRIBUTES TO 7M
annual chip deliveries



NG TECHNOLOGY IS IN 90%
of U.S. national security space satellites



OVER 50%
of production volume is commercial

ngc.com/micro

©2026 Northrop Grumman All Rights Reserved CS-23553
Approved for Public Release; NG26-0158

APPLICATIONS

- GaN20: Power applications through Ka-band
- GaN15: Power and low noise applications through V-band
- GaN09: Power and low noise applications through W-band
- GaN05 (in development): applications up to 200GHz

ADVANTAGES

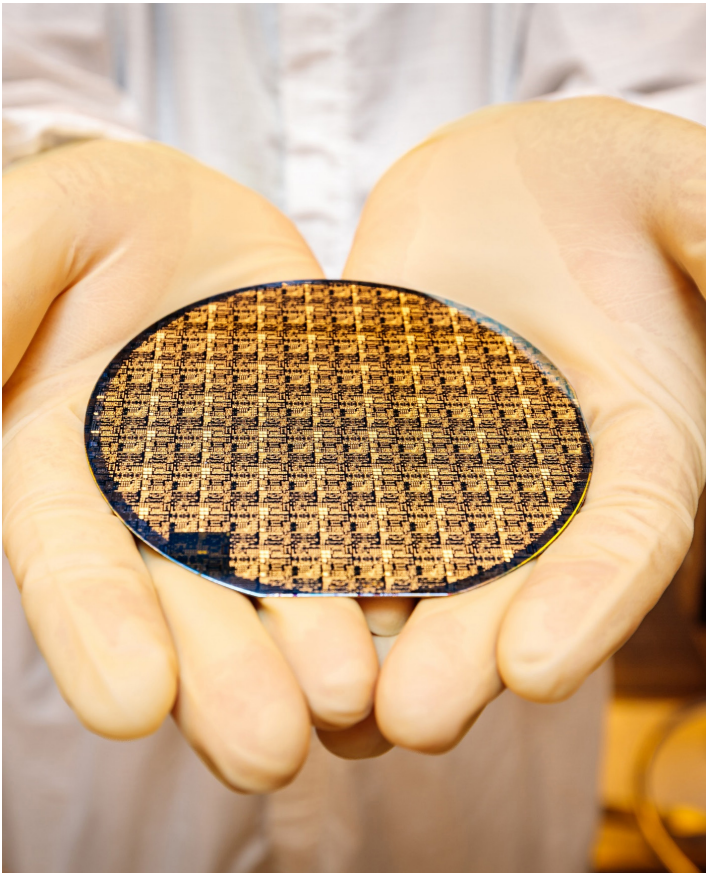
- Efficiency
- Size and weight
- High thermal conductivity

OUR LEADING TECHNOLOGY

Space Park Foundry focuses on products that are microscopic, modular, high speed, and low in power consumption and temperature. We are configured for R&D and prototyping, production and packaging.

III – V TECHNOLOGIES

- GaAs
 - GaN
 - InP
 - Chip-scale packaging (2.5 and 3D HI)
 - Products (Link to website)
 - Power amplifiers
 - Low Noise amplifiers
 - Mixers and Multipliers
- Switches
 - Services
 - 100mm wafer fabrication
 - Full suite of process design kits (PDK)
 - Dedicated and multi-customer shared mask runs
 - On -wafer RF testing to 220 GHz



FRONT-END FABRICATION	BACK-END PROCESSES	PROTOTYPE & DEVELOPMENT SUPPORT	ADVANCED PACKAGING PROCESSES	TESTING & CHARACTERIZATION
• Photolithography • Thin films • Etch • Diffusion • Ion Implantation • Molecular Beam Epitaxy • Electron Beam Lithography • Specialized processes for silicon, III-V, and advanced materials	• Thin film and electroplated metals • Bumping • Under bump metalization • Through wafer vias • Passivation • Wafer thinning • Dicing	• Pilot production for transitioning designs to production • Full suite of process design kits (PDK) • Dedicated and multi-customer shared mask runs	• Wafer Level Packaging • 3D heterogeneous chiplet integration • SiC Interposer	• Inline inspection • Electrical test • Yield analysis • Reliability screening



Explore our offerings



Shop our storefront

